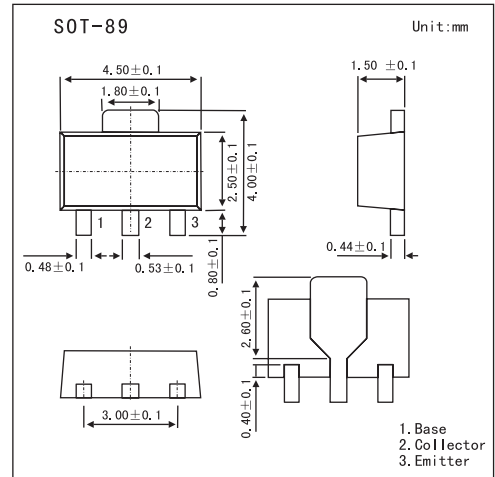


2SB1386

■ Features

- Low $V_{CE(sat)}$.
 $V_{CE(sat)} = -0.35V$ (Typ.)
($I_C/I_B = -4A / -0.1A$)
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-5	A
Collector current(Pulse)	I_{CP}^*	-10	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse, $P_w=10ms$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -50\mu A$	-30			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -1mA$	-20			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50\mu A$	-6			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20V$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V$			-0.5	μA
DC current transfer ratio	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.1A$			-1	V
Collector-emitter saturation voltage	h_{FE}	$V_{CE} = -2V, I_C = -0.5A$	82		390	
Transition frequency	C_{ob}	$V_{CE} = -6V, I_E = 50mA, f = 30MHz$		120		MHz
Output capacitance	f_r	$V_{CB} = -20V, I_E = 0A, f = 1MHz$		60		pF

■ h_{FE} Classification

Marking	BH		
	P	Q	R
h_{FE}	82~180	120~270	180~390